

ALJ13002

TRANSISTOR (NPN)

FEATURES

Power dissipation

P_{CM} : 1.25 W ($T_{amb}=25^{\circ}C$)

Collector current

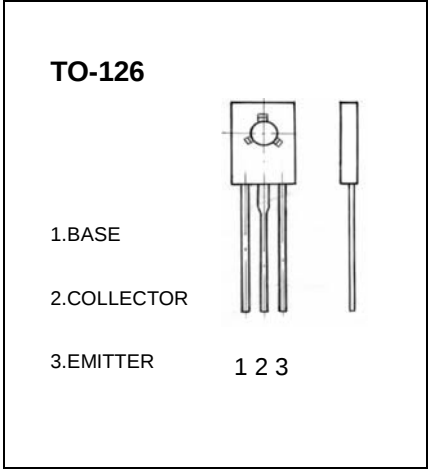
I_{CM} : 1 A

Collector-base voltage

$V_{(BR)CBO}$: 600 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 100\mu A, I_E = 0$	600			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 1mA, I_B = 0$	400			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 100\mu A, I_C = 0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB} = 600V, I_E = 0$			100	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 6V, I_C = 0$			100	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = 10V, I_C = 250\mu A$	5			
	$h_{FE(2)}$	$V_{CE} = 10V, I_C = 200mA$	9		40	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 200mA, I_B = 40mA$			0.8	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 200mA, I_B = 40mA$			1.1	V
Transition frequency	f_T	$V_{CE} = 10V, I_C = 100mA, f = 1MHz$	5			MHz
Fall time	t_f	$I_C = 1A, I_{B1} = -I_{B2} = 0.2A$ $V_{CC} = 100V$			0.5	μs
Storage time	t_s				2.5	μs

CLASSIFICATION OF $h_{FE(2)}$

Rank						
Range	9-15	15-20	20-25	25-30	30-35	35-40